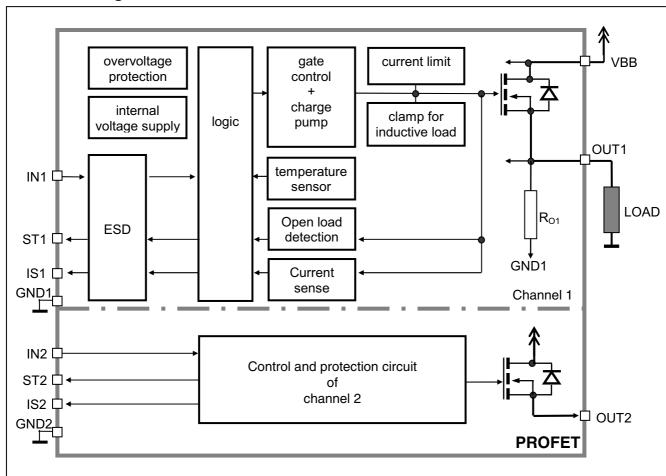


## **Functional diagram**



#### **Pin Definitions and Functions**

Pin	Symbol	Function
1,10,	$V_{bb}$	Positive power supply voltage. Design the
11,12,	~~	wiring for the simultaneous max. short circuit
15,16,		currents from channel 1 to 2 and also for low
19,20		thermal resistance
3	IN1	Input 1,2, activates channel 1,2 in case of
7	IN2	logic high signal
17,18	OUT1	Output 1,2, protected high-side power output
13,14	OUT2	of channel 1,2. Both pins of each output have
		to be connected in parallel for operation
		according ths spec (e.g. k <sub>iis</sub> ). Design the wiring
		for the max. short circuit current
4	ST1	Diagnostic feedback 1,2 of channel 1,2,
8	ST2	open drain, invers to input level
2	GND1	Ground 1 of chip 1 (channel 1)
6	GND2	Ground 2 of chip 2 (channel 2)
5	IS1	Sense current output 1,2; proportional to the
9	IS2	load current, zero in the case of current
		limitation of the load current

## Pin configuration



# **Maximum Ratings** at $T_i = 25^{\circ}$ C unless otherwise specified

Parameter	Symbol	Values	Unit
Supply voltage (overvoltage protection see page 5)	$V_{ m bb}$	43	V
Supply voltage for full short circuit protection $\Gamma_{j,\text{start}} = -40 \dots + 150^{\circ}\text{C}$	$V_{ m bb}$	34	V
oad current (Short-circuit current, see page 5)	<i>I</i> ∟	self-limited	Α
oad dump protection <sup>1)</sup> $V_{\text{LoadDump}} = V_{\text{A}} + V_{\text{S}}$ , $V_{\text{A}} = 13.5 \text{ V}$ $R_{\text{I}}^{(2)} = 2 \Omega$ , $t_{\text{d}} = 200 \text{ ms}$ ; IN = low or high, each channel loaded with $R_{\text{L}} = 7.0 \Omega$ ,	V <sub>Load dump</sub> <sup>3)</sup>	60	V
Operating temperature range Storage temperature range	$T_{\rm stg}$	-40+150 -55+150	°C
Power dissipation (DC) <sup>4)</sup> $T_a = 25^{\circ}\text{C}$ : (all channels active) $T_a = 85^{\circ}\text{C}$ :	P <sub>tot</sub>	3.8 2.0	W
Aximal switchable inductance, single pulse $V_{bb} = 12V$ , $T_{j,start} = 150^{\circ}C^{4}$ ,			
$I_{\rm L}$ = 5.5 A, $E_{\rm AS}$ = 370 mJ, $0\Omega$ one channel: $I_{\rm L}$ = 8.5 A, $E_{\rm AS}$ = 790 mJ, $0\Omega$ two parallel channels: see diagrams on page 10	Z <sub>L</sub>	18 16	mH
Electrostatic discharge capability (ESD) IN: (Human Body Model) ST, IS: out to all other pins shorted: acc. MIL-STD883D, method 3015.7 and ESD assn. std. S5.1-1993 R=1.5kΩ; C=100pF	V <sub>ESD</sub>	1.0 4.0 8.0	kV
nput voltage (DC)	V <sub>IN</sub>	-10 +16	V
Current through input pin (DC) Current through status pin (DC) Current through current sense pin (DC) see internal circuit diagram page 9	I <sub>IN</sub> I <sub>ST</sub> I <sub>IS</sub>	±2.0 ±5.0 ±14	mA

### **Thermal Characteristics**

Parameter and Conditions	Symbol	Values			Unit	
			min	typ	Max	
hermal resistance junction - soldering point <sup>4),5)</sup> junction - ambient <sup>4)</sup>	each channel: one channel active: all channels active:	R <sub>thjs</sub> R <sub>thja</sub>	  	 40 33	12  	K/W

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Supply voltages higher than  $V_{bb(AZ)}$  require an external current limit for the GND and status pins (a 150 $\Omega$  resistor for the GND connection is recommended.

 $R_{\rm I}$  = internal resistance of the load dump test pulse generator

<sup>)</sup> V<sub>Load dump</sub> is setup without the DUT connected to the generator per ISO 7637-1 and DIN 40839

Device on 50mm\*50mm\*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70μm thick) copper area for V<sub>bb</sub>



Parameter and Conditions, each of the two c	hannels <b>Symbol</b>		Values		
at T <sub>j</sub> = -40+150°C, $V_{bb}$ = 12 V unless otherwise specific	ecified	min	typ	max	
Load Switching Capabilities and Charact	eristics				
On-state resistance (V <sub>bb</sub> to OUT); I <sub>L</sub> = 5 A					
each channel, $T_i$	= 25°C:   <i>R</i> <sub>ON</sub>		27	30	mΩ
•	150°C:		54	60	
two parallel channels, $T_i$	= 25°C:		14	15	
Output voltage drop limitation at small load					
currents, see page 14	$V_{ON(NL)}$		50		mV
$I_{L} = 0.5 \text{ A}$ $T_{j} = -40$					
Nominal load current one channel	active: I <sub>L(NOM)</sub>	4.9	5.5		Α
two parallel channels	active:	7.8	8.5		
Device on PCB <sup>6</sup> ), $T_a = 85^{\circ}\text{C}$ , $T_i \leq 150^{\circ}\text{C}$					
Output current while GND disconnected or pul V <sub>bb</sub> = 30 V, V <sub>IN</sub> = 0, see diagram page 10	led up <sup>7)</sup> ;			8	mA
Turn-on time <sup>8)</sup> IN to 90%	$\sqrt{V_{\text{OUT}}}$ : $t_{\text{on}}$	25	70	150	μs
Turn-off time IN ☐ to 10%	$^{\prime}$ $V_{OUT}$ : $t_{off}$	25	80	200	
$R_{\rm L}$ = 12 $\Omega$					
Slew rate on 8)	d V/dt <sub>on</sub>	0.1		1	V/µs
10 to 30% $V_{\text{OUT}}$ , $R_{\text{L}} = 12 \Omega$ :					
Slew rate off <sup>8)</sup> 70 to 40% $V_{\text{OUT}}$ , $R_{\text{L}} = 12 \Omega$ :	-d V/dt <sub>off</sub>	0.1		1	V/µs
Operating Parameters	·				
Operating voltage <sup>9)</sup>	$V_{ m bb(on)}$	5.0		34	V
Undervoltage shutdown	V <sub>bb(under)</sub>	3.2		5.0	V
Undervoltage restart $T_j = -40$ $T_{j-} = +$			4.5	5.5 6.0	V
Undervoltage restart of charge pump see diagram page 13 $T_j = -40$	+25°C: V <sub>bb(ucp)</sub>		4.7 	6.5 7.0	V
Undervoltage hysteresis	$\Delta V_{ m bb(under)}$		0.5		V
$\Delta V$ bb(under) = $V$ bb(u rst) - $V$ bb(under)					
Overvoltage shutdown	$V_{ m bb(over)}$	34		43	V
Overvoltage restart	$V_{ m bb(o\ rst)}$	33			V

<sup>6)</sup> Device on 50mm\*50mm\*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70μm thick) copper area for V<sub>bb</sub> connection. PCB is vertical without blown air. See page 15

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<sup>7)</sup> not subject to production test, specified by design

<sup>8)</sup> See timing diagram on page 11.

<sup>9)</sup> At supply voltage increase up to  $V_{bb}$ = 4.7 V typ without charge pump,  $V_{OUT} \approx V_{bb}$  - 2 V



Parameter and Conditions, each	Symbol	Values			Unit	
at T <sub>j</sub> = -40+150°C, $V_{bb}$ = 12 V unless	s otherwise specified		min	typ	max	
						ı
Overvoltage hysteresis		$\Delta V_{ m bb(over)}$		1		V
Overvoltage protection <sup>10)</sup> /bb=40 mA	<i>T</i> <sub>j</sub> =-40: <i>T</i> <sub>j</sub> =+25+150°C:	$V_{ m bb(AZ)}$	41 43	 47	 52	V
Standby current <sup>11)</sup>	$T_{\rm j}$ =-40°C25°C:	I <sub>bb(off)</sub>		8	30	μΑ
$V_{IN} = 0;$	$T_{\rm j}$ =150°C:			24	50	
Leakage output current (include $V_{\text{IN}} = 0$	d in I <sub>bb(off)</sub> )	I <sub>L(off)</sub>			20	μΑ
Operating current <sup>12)</sup> , $V_{IN} = 5V$ ,						
$I_{\text{GND}} = I_{\text{GND1}} + I_{\text{GND2}},$	one channel on: two channels on:	I <sub>GND</sub>		1.2 2.4	3 6	mA
Protection Functions <sup>13)</sup>		T	· · · · · ·	ı		
Current limit, (see timing diagrams,						_
	$T_{\rm j} = -40^{\circ}{\rm C}$ :	I <sub>L(lim)</sub>	48	56	65	Α
	$T_{\rm j} = 25^{\circ}{\rm C}$ :		40	50	58	
	$T_{j} = +150^{\circ}C$ :		31	37	45	
Repetitive short circuit current li						ā
$T_{\rm j} = T_{ m jt}$	each channel	I <sub>L(SCr)</sub>		24		Α
	o parallel channels			24		
(see timing diagrams, page 12)						
Initial short circuit shutdown time	e $T_{j,start} = 25^{\circ}C$ :	toff(SC)		2.0		ms
	diagrams on page 12)					
Output clamp (inductive load sw at VON(CL) = Vbb - VOUT, IL= 40 mA	,	$V_{ m ON(CL)}$	41			٧
	<i>T</i> <sub>j</sub> =25°C150°C:		43	47	52	
Thermal overload trip temperatu	$T_{jt}$	150			°C	
Thermal hysteresis		$\Delta T_{\rm jt}$		10		K

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Supply voltages higher than  $V_{bb(AZ)}$  require an external current limit for the GND and status pins (a 150  $\Omega$  resistor in the GND connection is recommended). See also  $V_{ON(CL)}$  in table of protection functions and circuit diagram page 9.

<sup>11)</sup> Measured with load; for the whole device; all channels off

<sup>12)</sup> Add  $I_{ST}$ , if  $I_{ST} > 0$ 

Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

<sup>&</sup>lt;sup>14)</sup> If channels are connected in parallel, output clamp is usually accomplished by the channel with the lowest  $V_{ON(CL)}$ 



Parameter and Conditions, each of the two channels	oamya	values			Unit
at T <sub>j</sub> = -40+150°C, $V_{bb}$ = 12 V unless otherwise specified		min	typ	max	
Reverse Battery					
Reverse battery voltage 15)	-V <sub>bb</sub>			32	V
Drain-source diode voltage ( $V_{out} > V_{bb}$ ) $I_L = -4.0 \text{ A}, T_j = +150^{\circ}\text{C}$	-V <sub>ON</sub>		600		mV
Diagnostic Characteristics					
Current sense ratio <sup>16)</sup> , static on-condition,					
$V_{IS} = 05 \text{ V}, V_{bb(on)} = 6.5^{17}27 \text{V},$					
$k_{\text{ILIS}} = I_{\text{L}} / I_{\text{IS}}$ $T_{\text{j}} = -40^{\circ}\text{C}, I_{\text{L}} = 5 \text{ A}$ :	<i>k</i> <sub>ILIS</sub>	4350	4800	5800	
$T_{\rm j}$ = -40°C, $I_{\rm L}$ = 0.5 A:		3100	4800	7800	
$T_{\rm j}$ = 25+150°C, $I_{\rm L}$ = 5 A:		4350	4800	5350	
$T_{j}$ = 25+150°C, $I_{L}$ = 0.5 A:		3800	4800	6300	
Current sense output voltage limitation					
$T_{j} = -40 \dots +150^{\circ}\text{C}$ /IS = 0, /L = 5 A:	$V_{IS(lim)}$	5.4	6.1	6.9	V
Current sense leakage/offset current					
$T_{j} = -40 \dots + 150^{\circ}C$ $V_{N}=0, V_{S}=0, I_{L}=0$ :	I <sub>IS(LL)</sub>	0		1	μΑ
$V_{IN}=5 \text{ V}, V_{IS}=0, I_{L}=0$ :	I <sub>IS(LH)</sub>	0		15	
$V_{IN}=5 V$ , $V_{IS}=0$ , $V_{OUT}=0$ (short circuit)	I <sub>IS(SH)</sub> 18)	0		10	
Current sense settling time to $I_{IS \text{ static}} \pm 10\%$ after positive input slope <sup>18)</sup> , $I_{L} = 0$ 5 A	$t_{son(IS)}$			300	μs
Current sense settling time to 10% of $I_{IS}$ static after negative input slope <sup>18)</sup> , $I_{L} = 5$ 0 A	t <sub>soff(IS)</sub>		30	100	μs
Current sense rise time (60% to 90%) after change of load current <sup>18)</sup> $I_L = 2.5 - 5$ A	t <sub>slc(IS)</sub>		10		μs
Open load detection voltage <sup>19</sup> (off-condition)	V <sub>OUT(OL)</sub>	2	3	4	V
Internal output pull down (pin 17,18 to 2 resp. 13,14 to 6), VOUT=5 V	Ro	5	15	40	kΩ

<sup>15)</sup> Requires a 150  $\Omega$  resistor in GND connection. The reverse load current through the intrinsic drain-source diode has to be limited by the connected load. Power dissipation is higher compared to normal operating conditions due to the voltage drop across the drain-source diode. The temperature protection is not active during reverse current operation! Input and Status currents have to be limited (see max. ratings page 3 and circuit page 9).

This range for the current sense ratio refers to all devices. The accuracy of the  $k_{\text{\tiny LLIS}}$  can be raised at least by a factor of two by matching the value of  $k_{\scriptscriptstyle \rm ILIS}$  for every single device. In the case of current limitation the sense current  $I_{\rm IS}$  is zero and the diagnostic feedback potential  $V_{\rm ST}$  is High. See figure 2c, page 12.

<sup>&</sup>lt;sup>17)</sup> Valid if  $V_{\rm bb(u\ rst)}$  was exceeded before.

<sup>&</sup>lt;sup>18)</sup> not subject to production test, specified by design

<sup>19)</sup> External pull up resistor required for open load detection in off state



Parameter and Conditions, each of the two channels	Symbol		Values	}	Unit
at $T_j = -40+150$ °C, $V_{bb} = 12$ V unless otherwise specified		min	typ	max	

## Input and Status Feedback<sup>20)</sup>

	1_			. 1	
Input resistance	$ R_{l} $	3.0	4.5	7.0	$k\Omega$
(see circuit page 9)					
Input turn-on threshold voltage	$V_{IN(T+)}$			3.5	V
Input turn-off threshold voltage	$V_{\text{IN(T-)}}$	1.5			V
Input threshold hysteresis	$\Delta V_{\text{IN(T)}}$		0.5		V
Off state input current $V_{IN} = 0.4 \text{ V}$ :	I <sub>IN(off)</sub>	1		50	μΑ
On state input current $V_{IN} = 5 \text{ V}$ :	I <sub>IN(on)</sub>	20	50	90	μΑ
Delay time for status with open load	t <sub>d(ST OL3)</sub>		400		μs
after Input neg. slope (see diagram page 13)					
Status delay after positive input slope					
(not subject to production test, specified by design)	t <sub>don(ST)</sub>		13		μs
Status delay after negative input slope					
(not subject to production test, specified by design)	t <sub>doff(ST)</sub>		1		μs
Status output (open drain)					
Zener limit voltage $T_j = -40 + 150$ °C, $I_{ST} = +1.6$ mA:	V <sub>ST(high)</sub>	5.4	6.1	6.9	V
ST low voltage $T_i = -40 + 25^{\circ}\text{C}$ , $I_{ST} = +1.6 \text{ mA}$ :	V <sub>ST(low)</sub>			0.4	
ST low voltage $T_j = -40+25$ °C, $I_{ST} = +1.6$ mA: $T_j = +150$ °C, $I_{ST} = +1.6$ mA:				0.7	
Status leakage current, $V_{ST} = 5 \text{ V}$ , $T_{j}=25 \dots +150^{\circ}\text{C}$ :	I <sub>ST(high)</sub>			2	μA

 $<sup>^{20)}\,</sup>$  If ground resistors  $R_{\mbox{\footnotesize GND}}$  are used, add the voltage drop across these resistors.



#### Truth Table

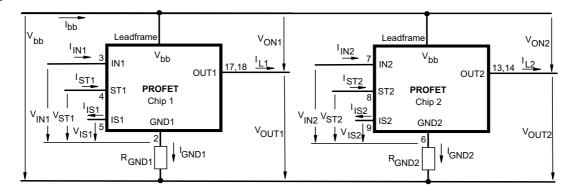
	Input 1	Output 1	Status 1	Current Sense 1
	Input 2	Output 2	Status 2	Current Sense 2
	level	level	level	I <sub>IS</sub>
Normal	L	L	Н	0
operation	Н	Н	L	nominal
Current-	L	L	Н	0
limitation	Н	Н	Н	0
Short circuit to	L	L	Н	0
GND	Н	L <sup>21</sup> )	Н	0
Over-	L	L	Н	0
temperature	Н	L	Н	0
Short circuit to	L	Н	L <sup>22</sup> )	0
V <sub>bb</sub>	Н	Н	L	<nominal <sup="">23)</nominal>
Open load	L	L <sup>24</sup> )	H (L <sup>25)</sup> )	0
	Н	Н	`L ´	0
Undervoltage	L	L	Н	0
	Н	L	L	0
Overvoltage	L	L	Н	0
	Н	L	L	0
Negative output	L	L	Н	0
voltage clamp				

L = "Low" Level H = "High" Level X = don't care

Z = high impedance, potential depends on external circuit Status signal after the time delay shown in the diagrams (see fig 5. page 13)

Parallel switching of channel 1 and 2 is possible by connecting the inputs and outputs in parallel. The status outputs ST1 and ST2 have to be configured as a 'Wired OR' function with a single pull-up resistor. The current sense outputs IS1 and IS2 have to be connected with a single pull-down resistor.

#### **Terms**



Leadframe (V<sub>bb</sub>) is connected to pin 1,10,11,12,15,16,19,20

External R<sub>GND</sub> optional; two resistors R<sub>GND1</sub>, R<sub>GND2</sub> = 150  $\Omega$  or a single resistor R<sub>GND</sub> = 75  $\Omega$  for reverse battery protection up to the max. operating voltage.

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The voltage drop over the power transistor is  $V_{\rm bb}$ - $V_{\rm OUT}$  > 3V typ. Under this condition the sense current  $I_{\rm IS}$  is

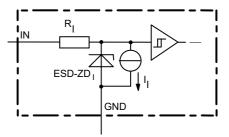
<sup>&</sup>lt;sup>22)</sup> An external short of output to V<sub>bb</sub>, in the off state, causes an internal current from output to ground. If R<sub>GND</sub> is used, an offset voltage at the GND and ST pins will occur and the  $V_{\text{ST low}}$  signal may be errorious.

Low ohmic short to  $V_{
m bb}$  may reduce the output current  $I_{
m L}$  and therefore also the sense current  $I_{
m IS}$ .

Power Transistor off. high impedance

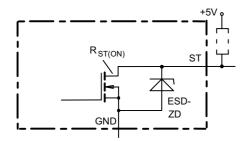


#### Input circuit (ESD protection), IN1 or IN2



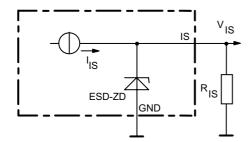
The use of ESD zener diodes as voltage clamp at DC conditions is not recommended.

### Status output, ST1 or ST2



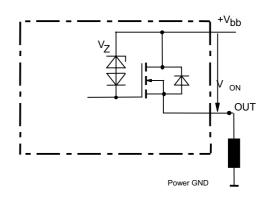
ESD-Zener diode: 6.1 V typ., max 5.0 mA;  $R_{ST(ON)}$  < 375  $\Omega$  at 1.6 mA. The use of ESD zener diodes as voltage clamp at DC conditions is not recommended.

#### **Current sense output**



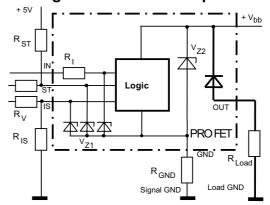
ESD-Zener diode: 6.1 V typ., max 14 mA;  $R_{\rm IS}$  = 1 k $\Omega$  nominal

# **Inductive and overvoltage output clamp,** OUT1 or OUT2



VON clamped to VON(CL) = 47 V typ.

#### Overvoltage and reverse batt. protection

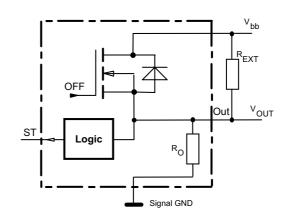


 $V_{Z1}$  = 6.1 V typ.,  $V_{Z2}$  = 47 V typ.,  $R_{GND}$  = 150 Ω,  $R_{ST}$ =15kΩ,  $R_{I}$ =4.5kΩ typ.,  $R_{IS}$ =1kΩ,  $R_{V}$ =15kΩ, In case of reverse battery the current has to be limited by the load. Temperature protection is not active

#### Open-load detection OUT1 or OUT2

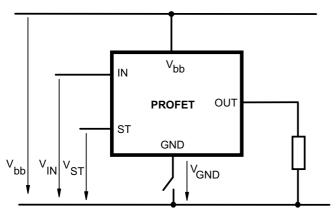
OFF-state diagnostic condition:

 $V_{\text{OUT}} > 3 \text{ V typ.}$ ; IN low



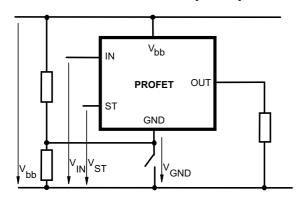


#### GIAD MISCOMMEC



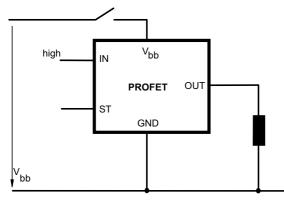
Any kind of load. In case of IN = high is  $V_{OUT} \approx V_{IN} - V_{IN}(T_+)$ . Due to  $V_{GND} > 0$ , no  $V_{ST} = low$  signal available.

### GND disconnect with GND pull up



Any kind of load. If  $V_{GND} > V_{IN} - V_{IN(T+)}$  device stays off Due to  $V_{GND} > 0$ , no  $V_{ST} = low$  signal available.

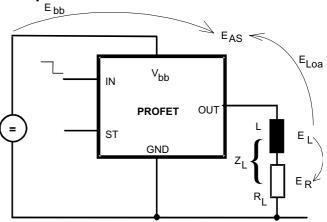
# V<sub>bb</sub> disconnect with energized inductive load



For inductive load currents up to the limits defined by  $Z_L$  (max. ratings and diagram on page 10) each switch is protected against loss of  $V_{hb}$ .

Consider at your PCB layout that in the case of Vbb disconnection with energized inductive load all the load current flows through the GND connection.

# dissipation



Energy stored in load inductance:

$$E_L = \frac{1}{2} \cdot L \cdot I_L^2$$

While demagnetizing load inductance, the energy dissipated in PROFET is

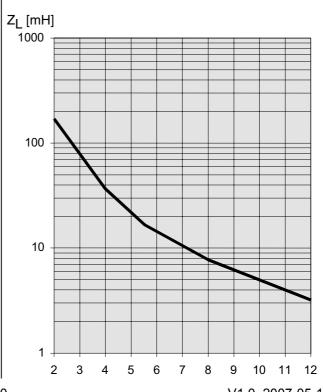
$$E_{AS} = E_{bb} + E_L - E_R = V_{ON(CL)} \cdot i_L(t) dt$$

with an approximate solution for  $R_I > 0 \Omega$ :

$$E_{AS} = \frac{I_L \cdot L}{2 \cdot R_L} \left( V_{bb} + |V_{OUT(CL)}| \right) ln \left( 1 + \frac{I_L \cdot R_L}{|V_{OUT(CL)}|} \right)$$

# Maximum allowable load inductance for a single switch off (one channel)<sup>4)</sup>

$$L = f(I_L)$$
; T<sub>i,start</sub> = 150°C, V<sub>bb</sub> = 12 V, R<sub>L</sub> = 0  $\Omega$ 

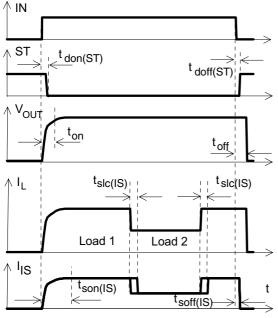




# **Timing diagrams**

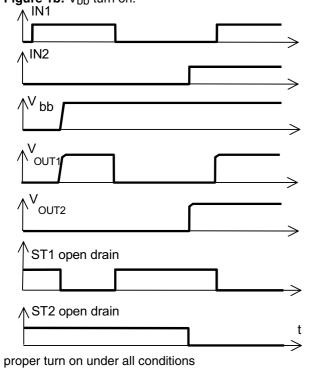
Both channels are symmetric and consequently the diagrams are valid for channel 1 and channel 2

**Figure 1a:** Switching a resistive load, change of load current in on-condition:



The sense signal is not valid during settling time after turn or change of load current.

Figure 1b: V<sub>bb</sub> turn on:



**Figure 2a:** Switching a resistive load, turn-on/off time and slew rate definition:

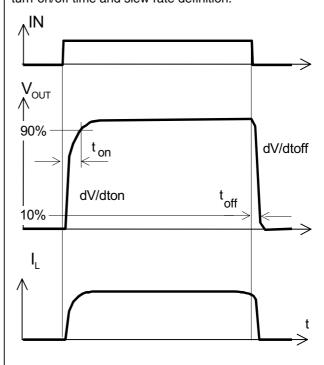
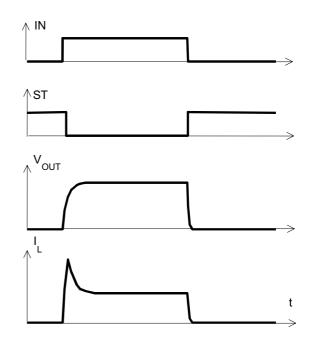


Figure 2b: Switching a lamp:



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Figure 2c: Switching a lamp with current limit:

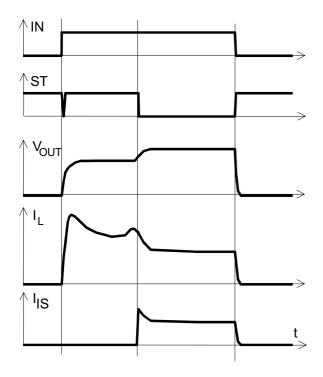
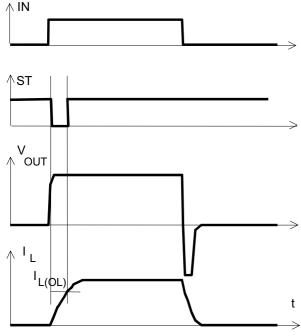
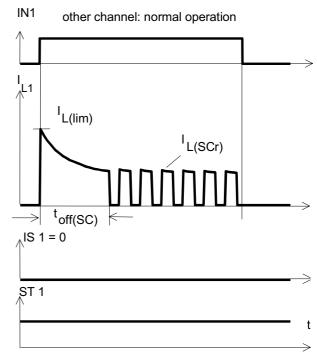


Figure 2d: Switching an inductive load



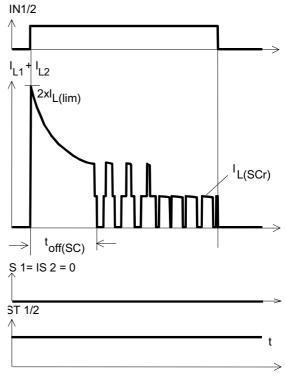
\*) if the time constant of load is too large, open-load-status may occur

**Figure 3a:** Turn on into short circuit: shut down by overtemperature, restart by cooling



Heating up of the chip may require several milliseconds, depending on external conditions

**Figure 3b:** Turn on into short circuit: shut down by overtemperature, restart by cooling (two parallel switched channels 1 and 2)

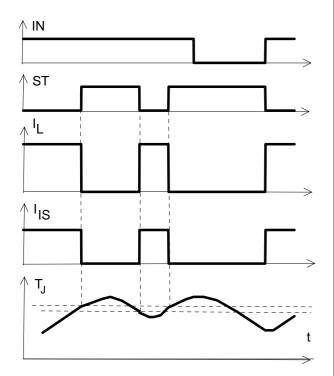


ST1 and ST2 have to be configured as a 'Wired OR' function ST1/2 with a single pull-up resistor

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**Figure 4a:** Overtemperature: Reset if  $T_i < T_{it}$ 



**Figure 5a:** Open load: detection (with R<sub>EXT</sub>), turn on/off to open load

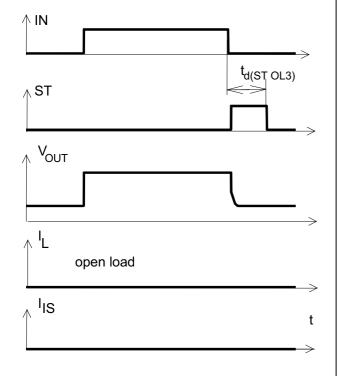


Figure 6a: Undervoltage:

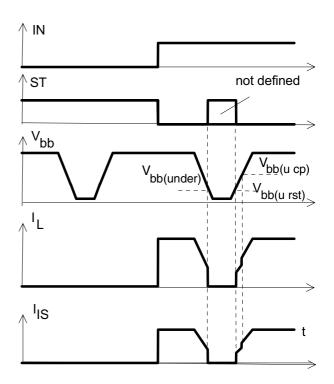
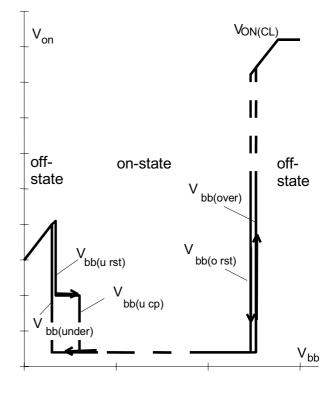


Figure 6b: Undervoltage restart of charge pump



charge pump starts at  $V_{\rm bb(ucp)}$  =4.7 V typ.



Figure 7a: Overvoltage:

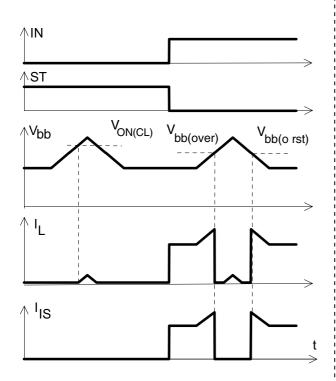
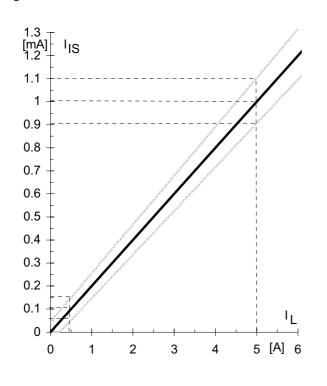


Figure 8a: Current sense versus load current<sup>26</sup>::



This range for the current sense ratio refers to all devices. The accuracy of the  $k_{\rm max}$  can be raised at

Figure 8b: Current sense ratio:

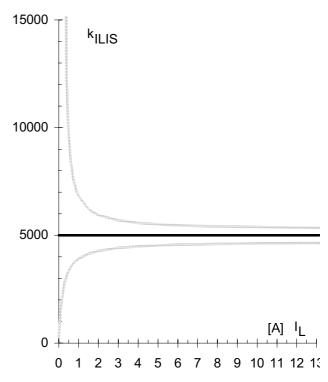
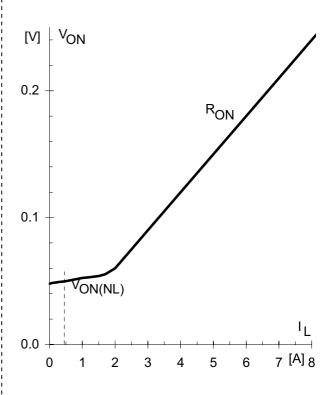


Figure 9a: Output voltage drop versus load current:



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# **Package Outlines**

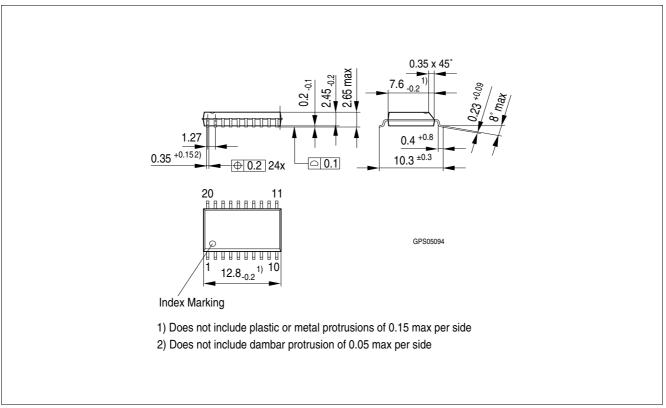


Figure 1 PG-DSO-20 (Plastic Dual Small Outline Package) (RoHS-compliant)

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (i.e Pb-free finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020).

Please specify the package needed (e.g. green package) when placing an order



# **Revision History**

Version	Date	Changes
1.0	2007-05-13	Creation of the green datasheet.
-		

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Edition 2007-05-13

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